Toshiba Bipolar Linear Integrated Circuit Multi-Chip

TA8493F, TA8493AF, TA8493BF

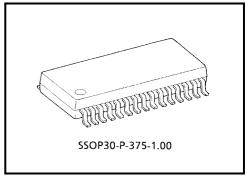
3-Phase Full Wave Brushless DC Motor Driver IC for CD-ROM Drives

These 3-phase, full-wave, brushless DC motor driver ICs have been developed for use in CD-ROM drive spindle motors. The TA8493F/AF/BF contain in its upper stage a discrete power transistor (P-ch-MOS) and uses direct PWM control system, which enables the IC to provide superior thermal efficiency.

Furthermore, the multi-chip structure of this device facilitates dispersion of the heat generated inside the package, making it possible to suppress heat concentration.

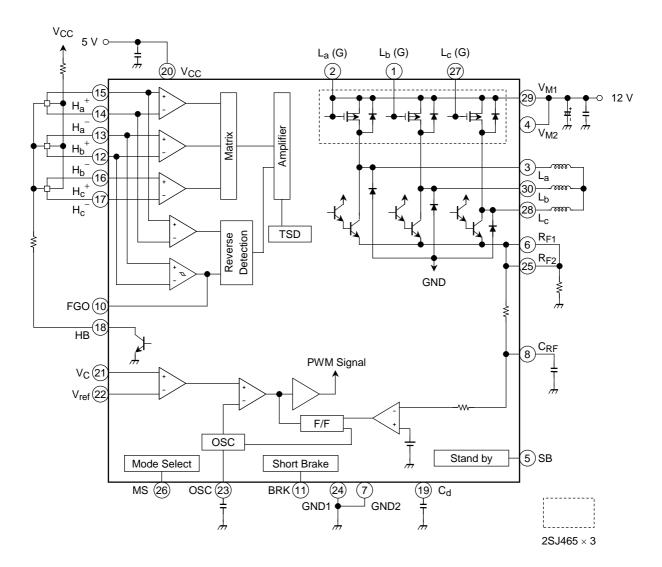
Features

- Multi-chip structure (3 × 2SJ465 chips built-in)
- Direct PWM control system
- Drive system: 120° drive system (TA8493F/BF)
 : 180° drive system (TA8493AF)
- Built-in current limiter: $I_{LIM} = 0.7 \text{ A (typ.)}$ (at $R_F = 0.33 \Omega$)
- Built-in reversing brake/short brake functions
- FG signal output (using hall element output signal)
- Built-in hall bias
- Built-in thermal shutdown circuit
- Package: MFP-30



Weight: 0.63 g (typ.)

Block Diagram



9 pin: N.C.



PIN Assignment

Terminal No.	Terminal Symbol	Function	Remarks
1	L _b (G)	b-phase upper side power transistor (base) output terminal	Keep open.
2	L _a (G)	a-phase upper side power transistor (base) output terminal	Keep open.
3	L _a	a-phase output terminal	Connect to the coil.
4	V _{M2}	Supply voltage terminal for motor drive	Connect to V _{M1} externally.
5	SB	RUN/STOP control terminal	H: RUN, L: STOP
6	R _{F1}	Output current detection terminal	Sets limiter current value. Connect to R _{F2} externally and between this terminal and GND.
7	GND2	GND	_
8	C _{RF}	Output current filter terminal	Connect a capacitor between this terminal and GND.
9	N.C.		
10	FGO	FG amplifier output terminal	Outputs a signal whose frequency is determined by the CD rotation frequency.
11	BRK	Brake mode select terminal	Output mode when V _C > V _{ref}
12	H _b ⁻	b-phase negative hall signal input terminal	Connect to hall element output terminal.
13	H _b ⁺	b-phase positive hall signal input terminal	Connect to hall element output terminal.
14	H _a ¯	a-phase negative hall signal input terminal	Connect to hall element output terminal.
15	H _a ⁺	a-phase positive hall signal input terminal	Connect to hall element output terminal.
16	H _c ⁺	c-phase positive hall signal input terminal	Connect to hall element output terminal.
17	H _c	a-phase negative hall signal input terminal	Connect to hall element output terminal.
18	НВ	Hall element bias terminal	Open collector output. Connect to the negative side of hall element bias line.
19	C _d	Forward/reverse changeover gain adjustment terminal	Adjust a rotation direction changeover gain
20	Vcc	Supply voltage terminal for control circuits	V _{CC (opr)} = 4.5 to 5.5 V
21	V _C	Control amplifier input terminal	Use the control signal as input.
22	V_{ref}	Control amplifier reference voltage input terminal	Use the reference voltage for the control amplifier as input.
23	osc	Triangular wave oscillation terminal	Connect a capacitor between this terminal and GND.
24	GND1	GND	_
25	R _{F2}	Output current detection terminal	Sets limiter current value. Connect to R _{F1} externally and between this terminal and GND.
26	MS	Mode select terminal	Determines output mode.
27	L _C (G)	c-phase upper side power transistor (base) output terminal	Keep open.
28	L _c	c-phase output terminal	Connect to the coil.
29	V _{M1}	Supply voltage terminal for motor drive	Connect to V _{M2} externally.
30	L _b	b-phase output terminal	Connect to the coil.

3 2002-01-31

Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit	
Power Supply Voltage	V _{CC}	7	V	
Tower Supply Voltage	V _M	16	V	
Output Current	Io	1.5	А	
Power Dissipation	P _D 1.0		W	
·	(Note1)			
Junction Temperature	Tj	150	°C	
Operating Temperature	T _{opr}	-20 to 75	°C	
Storage Temperature	T _{stg}	-55 to 150	°C	

Note1: unmounted

Operating Voltage Range

Characteristics	Symbol	Operating Range	Unit
Power Supply Voltage	V _{CC}	4.5 to 5.5	V
Tower Supply Vollage	V _M	10 to 14	V

Electrical Characteristics ($V_{CC} = 5 \text{ V}, V_{M} = 12 \text{ V}, Ta = 25^{\circ}\text{C}$)

Characteristics		Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit	
Supply Voltage		I _{CC1}	1	Stop mode	_	0.3	8.0	mA	
Supply Voltage		I _{CC2}] '	Run mode, output open	_	7	15	IIIA	
	Input Current	I _{INH}		V _{CMRH} = 2.5 V, (sink current)		_	2	μА	
Hall Amp.	Common Mode Input Voltage Range	V _{CMRH}	2	_	1.5		4.0	V	
	Input Amplitude	V_{H}		_	100	_	_	mV_{p-p}	
Hall Element Bias	s Saturation Voltage	V_{HB}	2	I _{HB} = 10 mA		1.3	2.0	V	
	Common Mode Input Voltage Range	V _{CMRC}	2		0.5	_	4.0	V	
	Input Current	I _{INC}		V _C = V _{ref} = 1.65 V, (source current)			5.0	μА	
Control Amp.	Dead Zone Voltage Width	V_{DZ}	_	V_{ref} = 1.65 V, R_F = 0.33 Ω (Note2)		100	_		
	Input Offset	ΔV _{OFF} (F)	2	CW mode, V_{ref} = 1.65 V, R_F = 0.33 Ω	20	50	150	mV	
	Voltage	ΔV _{OFF} (R)	2	CCW mode, $V_{ref} = 1.65 \text{ V}$, $R_F = 0.33 \ \Omega$	20	50	150		
Current Limit	Limit Current	I _{LIM}	_	$R_F = 0.33 \Omega$ (Note2)	_	700	_	mA	
Amp.	Lillit Culterit	V _{LIM}	3	_	0.25	0.3	0.35	V	
	Input Voltage (H)	V _{INS (H)}		(RUN)	3.0	_	Vcc	V	
RUN/STOP Control Circuit	Input Voltage (L)	V _{INS (L)}	1	(STOP)	GND	_	1.0]	
	Input Current	I _{INS (L)}		V _{INS} = GND, (source current)		_	1	μА	

Note2: this is not tested.

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Characteristics		Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
	Output Resistance (upper side)	R _{ON (U)}	4	I _O = 0.6 A	_	0.5	1.0	Ω
Output Circuit	Saturation Voltage (lower side)	V _{SAT (L)}	7	I _O = 0.6 A	_	0.4	0.8	V
	Cut-off Current (upper side)	I _{L (U)}	- 5	V _L = 16 V	_	_	10	пΔ
	Cut-off Current (lower side)	I _{L (L)}	3	V _L = 16 V	_	_	10	μΑ
	Input Voltage (H)	V _{MS (H)}		CCW mode $V_{C} > V_{ref}, BRK: L$	3.0	_	Vcc	V
Mode Select Circuit	Input Voltage (L)	V _{MS (L)}	6	Reversing brake mode V _C > V _{ref} , BRK: L	_	_	0.5	V
	Input Current	I _{INMS}]	V _{MS} = GND, (source current)	_	_	1	μА
	Hysteresis Voltage	V _{HYS}	8	_	5	20	45	mV _{p-p}
FG Amp.	Output Voltage (H)	V _{OFG} (H)	- 7	Source current: 10 μA	V _{CC} - 0.5	_	_	V
	Output Voltage (L)	V _{OFG (L)}		Sink current: 10 μA	_	_	0.5	V
	Input Voltage (H)	V _{BRK} (H)		_	3.0	_	V_{CC}	V
Short Brake Circuit	Input Voltage (L)	V _{BRK} (L)	6	_	_	_	0.5	v
	Input Current	I _{INBRK}		V _{BRK} = GND, (source current)	_	_	1	μΑ
Triangular Oscillation Circuit	Oscillation Frequency	fosc	_	C = 560 pF (Note2)	_	39	_	kHz
Thermal Shut-down Operating Temperature		TSD	_	Junction temperature (according to design specification) (Note2)	_	175		°C

Note2: this is not tested.

5 2002-01-31

Function Table

			Forward				Reverse	•
Ha	H _b	H _c	La	L _b	L _c	La	L _b	L _c
Н	L	L	Н	L	М	L	Н	М
Н	Н	L	Н	М	L	L	М	Н
L	Н	L	М	Н	L	М	L	Н
L	Н	Н	L	Н	М	Н	L	М
L	L	Н	L	М	Н	Н	М	L
Н	L	Н	М	L	Н	М	Н	L

<Forward>

<Reverse>

$$L_a = -(H_c - H_a)$$

$$L_b = -(H_a - H_b)$$

$$L_a = (H_c - H_a)$$

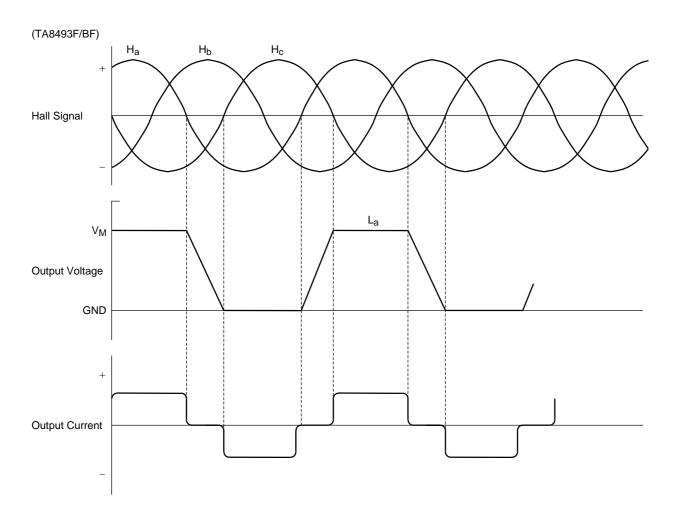
$$L_b = (H_a - H_b)$$

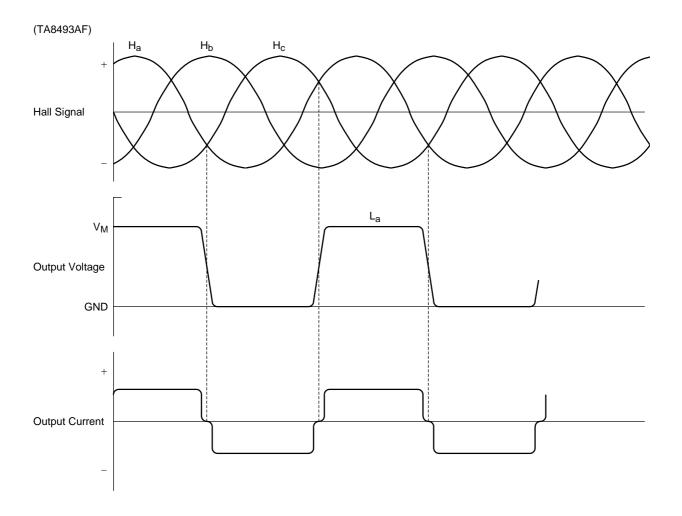
$$L_c = -(H_b - H_c)$$

$$L_c = (H_b - H_c)$$

Timing Diagram

<Forward>

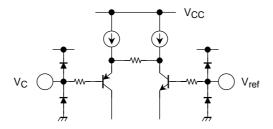




Functional Description

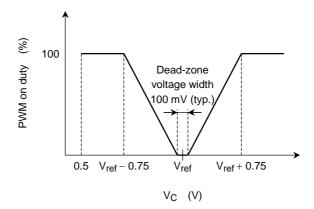
This IC is a 3-phase, full wave brushless DC motor driver of the direct PWM control type.

• Control amp input circuit

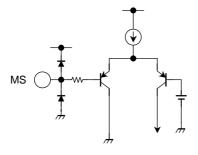


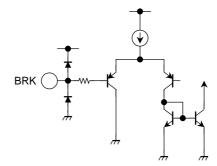
The common mode input voltage ranges for both VC and V_{ref} are 0.5 to 4.0 V. Relation between control input and PWM ON duty is shown below, PWM ON duty is 100% when $|V_{ref} - V_C| = 0.75$ V (typ.)

The input is provided with a dead-zone area whose voltage width is 100 mV (typ.)



• Mode select/short brake circuit





When $V_C > V_{ref}$, one of three modes (reverse rotation, reversing brake or short brake mode) can be selected by setting the MS and BRK pins appropriately.

<Function>

 $V_C < V_{ref}$

		BF	RK
		Н	L
MS	Н	Forward	Forward
IVIS	L	Forward	Forward

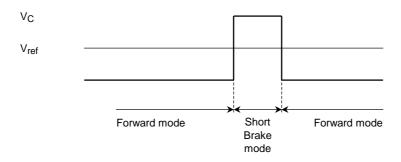
 $V_C > V_{ref}$

		BF	RK
		Н	L
MS	Н	Short brake	Reverse
	L	Short brake	Reversing brake

In Short Brake mode, the upper-stage power transistor is turned on and the lower-stage power transistor is turned off.

(short brake)

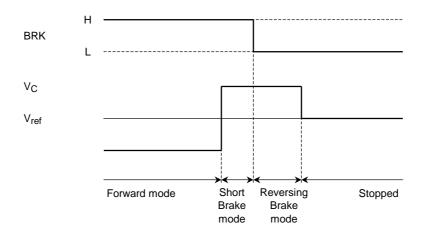
MS: H or L, BRK: H



(reversing brake)

(1) When stopping the motor by applying a reversing brake after a short brake

MS: L

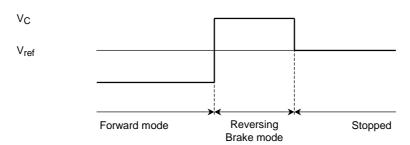


9

2002-01-31

(2) When stopping the motor using reversing brake mode

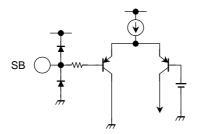
MS: L, BRK: L



Note3: For an explanation of the Reversing Brake mode stopping sequence, refer to the explanation of the reverse rotation detection circuit.

The short brake generates less heat than the reversing brake. Therefore Toshiba recommends a combined use of the short and reversing brakes when stopping the motor.

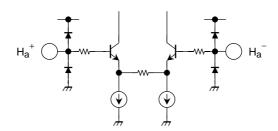
• Run/stop control circuit



When the driver IC is standing by, all of its circuits except the FG amp and the hall amp are turned off.

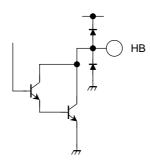
H: start L: standby

• Hall amp circuit



The common mode input voltage range for $V_{\mbox{CMRH}}$ is 1.5 to 4.0 V.

• Hall element bias circuit



The hall element bias current is turned off when the driver IC is in standby state.

Make sure that the negative hall bias line is connected to the HB pin.

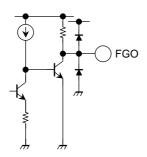
The remaining voltage is as follows:

$$V_{HB} = 1.2 V \text{ (typ.)}$$
 at $I_{HB} = 10 \text{ mA}$

Furthermore, this circuit cannot be used if FG output is necessary in standby state.

When the HB terminal is not used, the negative hall bias line must be connected to GND with a resistor in between

• FG amp circuit



This circuit uses a hall element signal which is output to FGO after a Schmitt stage.

The FG amp has a hysteresis of 20 mV_{p-p} (typ.) and its output voltages are

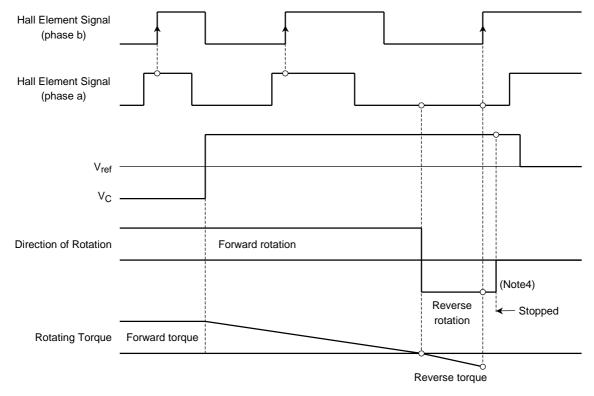
High level: $V_{CC} - 0.5$ to V_{CC} [V]

Low level: GND to 0.5 V $\,$ at IoFG = 10 μA

The FG amp is active when it is in standby state. When the hall element signal is input, the FG signal is output.

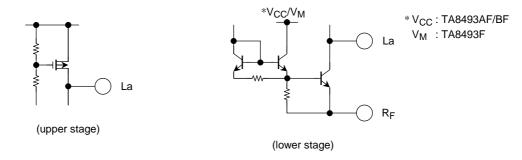
• Reverse rotation detection circuit

By comparing the two phases of the Hall element signal, this circuit detects a state where the phases are inverted, at which time the torque is reduced to 0. The detection accuracy is determined by the number of pulses per rotation of Hall element output.



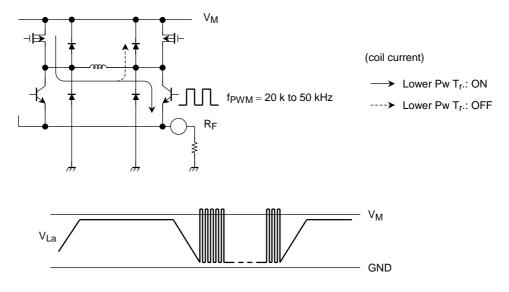
Note4: Due to its inertial force, the motor does not stop immediately after the torque is reduced to 0.

• Output circuit



This circuit uses the system to chop the lower power transistors and resurrect coil current through upper stage diodes.

The upper-stage power transistors consists of Pch-MOS transistors (2SJ465), which give high torque efficiency.



Note: Lower-stage predrivers of TA8493AF/BF are supplied by V_{CC} to reduce the power dissipation.

• Triangular wave oscillator circuit

Triangular waves are generated by connecting a capacitor between the OSC pin and GND.

This circuit is current output type, which makes PWM signal by comparing its output current with control amp output current.

$$f_{OSC} [Hz] = \frac{50 \times 10^{-6} [A]}{(3.0 - 0.7) [V] \times C [F]}$$



Taking into account efficiency considerations and the effects of noise, Toshiba recommends using the IC with an oscillation frequency of 20 kHz to 50 kHz.



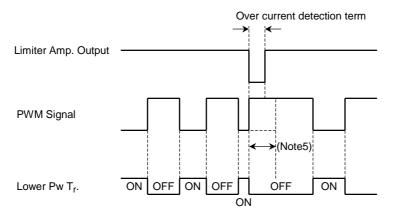
• Current limiter circuit

The current limit value is determined by the equation below.

$$I_{\rm LIM} \simeq \frac{0.3}{{\rm R_F} + 0.1} ~{\rm [A]~(typ.)}$$

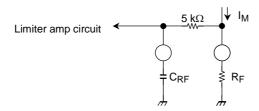
This circuit cut off lower power transistors compulsorily when filtered V_{RF} is more than reference voltage. (0.3 V)

PWM signal cut off compulsorily is released from OFF state by next ON signal.



Note5: Keep "H" level in this term

Consider inside resistance (5 k Ω) when setting the capacitance value (CRF).



• Thermal shut down circuit

The circuit turns off output when $T_j = 175$ °C (typ.) (according to design specification)



External Parts

Terminal No.	Function	Recommended Value	Remarks
C ₁	Power supply line oscillation prevention	0.22 μF	_
C ₂	Power supply line noise prevention	100 pF to 1000 pF	(Note6)
C ₃	Power supply line noise prevention	10 μF to 33 μF	(Note6)
C ₄	Filter	470 pF	_
C ₅	Forward/reverse changeover gain adjustment	0.01 μF	(Note7)
C ₆	Triangular wave oscillation	470 pF to 1000 pF	_
R ₁	Hall element bias	_	(Note8)
R ₂	Control amp reference voltage	_	(Note9)
R ₃	Output current detection	0.25 Ω to 0.5 Ω	_

Note6: Absorb switching noise by C_2 and C_3 .

Note7: This is used to adjust the rotation direction changeover gain.

This capacitance valve and the gain are in inverse.

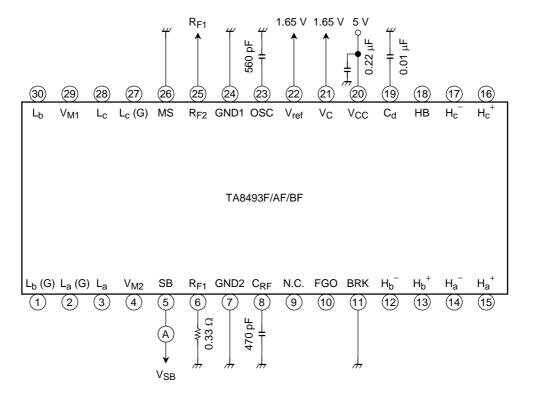
This capacitance is to prevent from output through current.

Note8: Be sure to set this bias so that the hall element output amplitude and common mode input voltage fall within the ranges specified in the table of electrical characteristic.

Note9: The voltage must be set to fall within the common mode input voltage range of the control amp.

Test Circuit

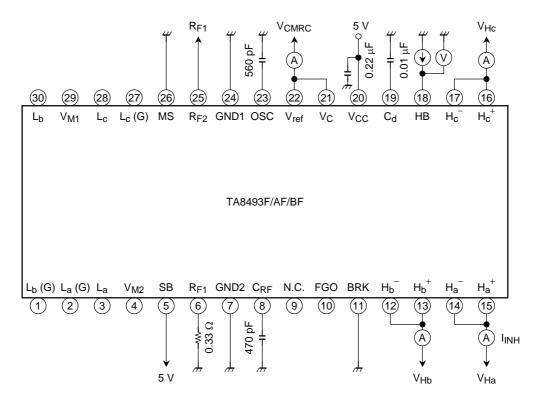
1. I_{CC1} , I_{CC2} , $V_{INS (H)}$, $V_{INS (L)}$, I_{INS}



- ICC1: VSB = 0.5 V
- ICC2: VSB = 3.0 V
- $\bullet~$ VINS (H), VINS (L): Judged by the gap between ICC1 and ICC2
- IINS: VINS = 0 V

2002-01-31

2. I_{INH}, I_{CMRH}, V_{HB}, I_{INC}, V_{CMRC}

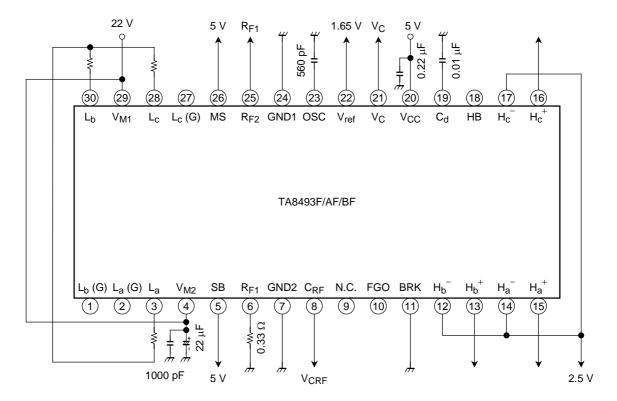


• IINH: Total of a phase negative and positive input current.

$$V_{Ha} = V_{Hb} = V_{Hc} = 2.5 \ V$$

- VCMRH: Measure the IINH gap between V_{Ha} = 1.5 V and V_{Ha} = 4.0 V. b and c phase are measured the same method.
- V_{HB}: I_{HB} = 10 mA
- VINC: Total of VC and Vref input current. At VCMRC = 1.65 V.
- VCMRC: Measure the IINC gap between VCMRC = 0.5 V and VCMRC = 4.0 V.

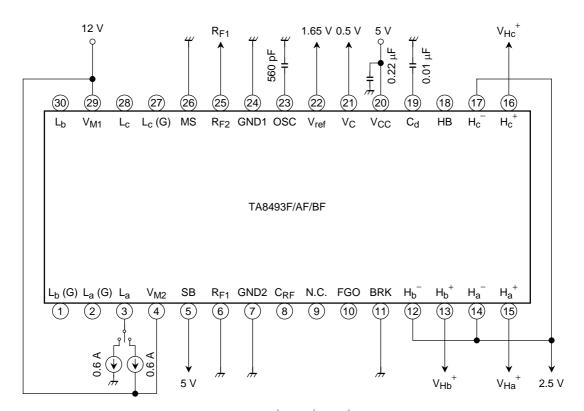
3. $\Delta V_{OFF(F)}$, $\Delta V_{OFF(R)}$, V_{LIM}



- ΔV_{OFF} (F): Measure VRF at VC = 1.63 V/1.5 V.
- ΔV_{OFF} (R): Measure VRF at VC = 1.67 V/1.8 V.
- V_{LIM} : Switch the V_{CRF} from 0 V to 0.4 V.

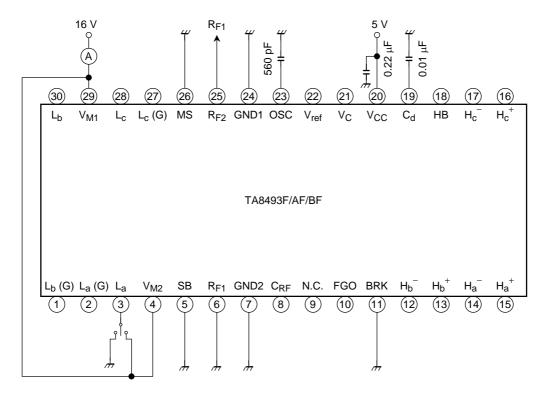
Measure the VCRF at the point when output voltage level changes from low (L) to high (H)

4. R_{ON (U)}, V_{SAT (L)}



- RON (U): Determined output function by VHa⁺, VHb⁺, VHc⁺ (2.45 V/2.55 V).
 Measure voltage value between VM and La, and change to resistance valve. b phase and c phase are measured the same method.
- $V_{SAT \; (L)} \label{eq:VSAT (L)} \label{eq:VSAT (L)} \label{eq:VSAT (L)} \label{eq:VSAT (L)} \label{eq:VSAT (L)} We assure voltage value between \; L_a \; and \; GND. \; b \; phase \; and \; c \; phase \; are \; measured \; the same method.$

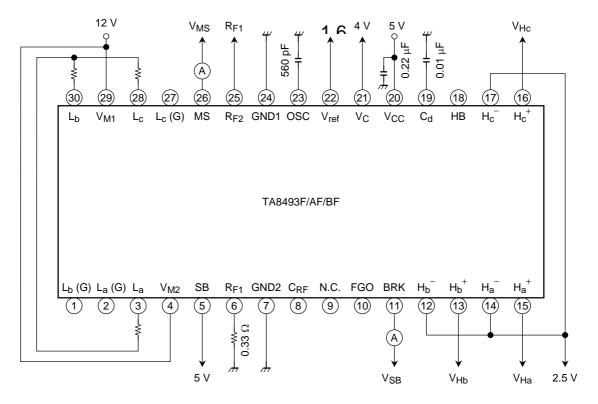
5. I_{L (U)}, I_{L (L)}



- $\bullet \quad I_{L\,(U)}\hbox{:}\ Measure\ I_{M}\ when\ L_{a}\ and\ GND\ are\ shorted.\ b\ phase\ and\ c\ phase\ are\ measured\ the\ same\ method.$
- $\bullet\quad I_L\,(\underline{\text{L}})\hbox{: Measure I_M when V_M and L_a are shorted. b phase and c phase are measured the same method.}$

20 2002-01-31

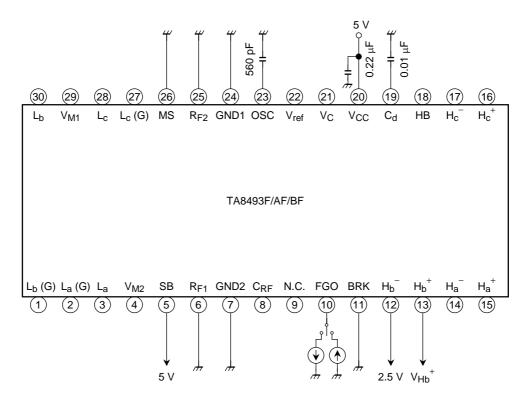
6. V_{MS} (H), V_{MS} (L), I_{INS}, V_{BRK} (H), V_{BRK} (L), I_{INBRK}



- VMS (H): VMS = 3.0 V, VBRK = 0 V, verify that output function is reverse mode.
- V_{MS} (L): V_{MS} = 0.5 V, V_{BRK} = 0 V, switch from foward mode to reverse mode by V_{Ha} , V_{Hb} V_{Hc} . Verify that V_{RF} changes to zero.

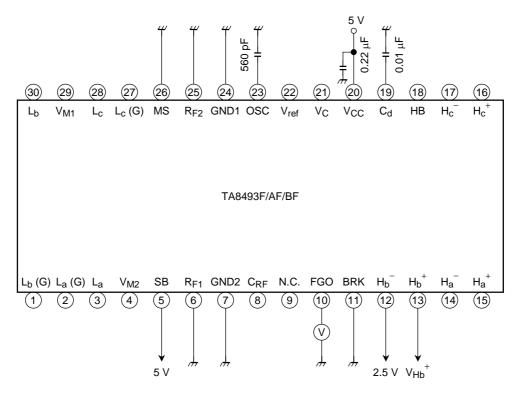
- IMS (L): VMS = 0 V, VBRK = 0 V
- V_{BRK} (H): $V_{MS} = 5$ V, $V_{BRK} = 3.0$ V, verify that $L_a = L_b = L_c$: H
- V_{BRK} (L): V_{MS} = 5 V, V_{BRK} = 0.5 V, verify that output function is reverse mode.

7. V_{OFG (H)}, V_{OFG (L)}



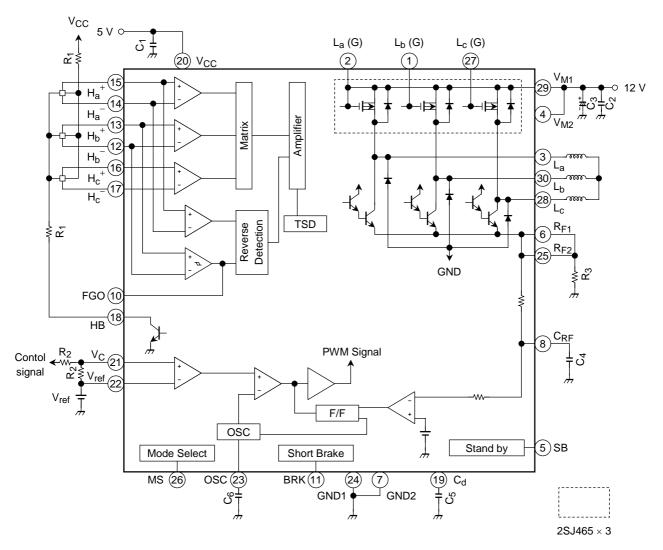
- VOFG (H): V_{Hb}^+ = 2.53 V, IFGO = 10 μA (source) VOFG (L): V_{Hb}^+ = 2.47 V, IFGO = 10 μA (sink)

8. V_{HYS}



VHYS: Switch the VHb⁺ from high (H) to low (L) and from (L) to (H). Measure the V_{Hb}⁺ at the point when FGO function changes.

Application Circuit



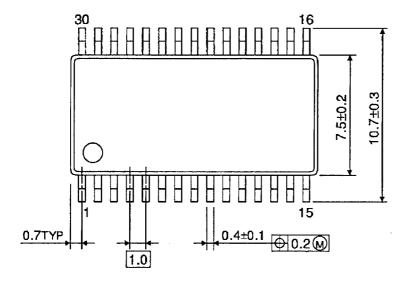
Note10: Utmost care is necessary in the design of the output line, V_{CC} , V_{M} and GND line since IC may be destroyed due to short-circuit between outputs, air contamination fault, or fault by improper grounding.

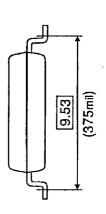
Unit: mm

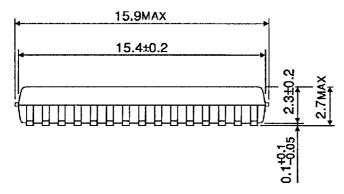
Package Dimensions

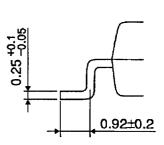
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Weight: 0.63 g (typ.)

RESTRICTIONS ON PRODUCT USE

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 In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability Handbook" etc..
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